

HCS06FH120E2C1

1200V/6mΩ Half Bridge SiC MOSFET Module

Description

The HCS06FH120E2C1 is a Half Bridge SiC MOSFET half bridge Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Solar Inverter, UPS, Fuel cell- DC/DC converter, Energy storage Systems.



Features

- Blocking voltage : 1200V
- $R_{ds(on)}$ 6.5 mΩ @ $T_j = 25^{\circ}C$
- 200A@ $T_f = 90^{\circ}C$
- Low Switching Losses
- 175 °C maximum junction temperature
- Si₃N₄ AMB
- Thermistor inside

Applications

- Solar inverter Systems
- Fuel cell -DC/DC converter
- Uninterruptible Power Supplier
- Energy Storage Systems

Circuit diagram

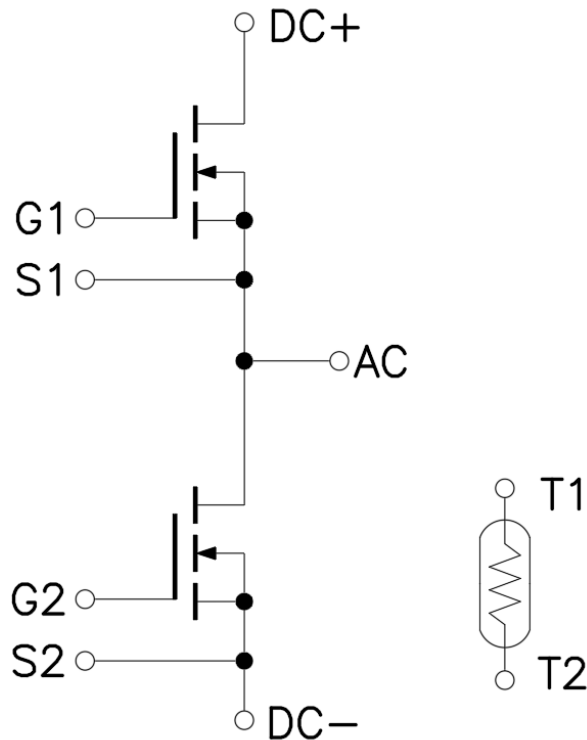


Figure 1. Outdrawing & circuit diagram for HCS06FH120E2C1

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Pin Configuration and Function Description

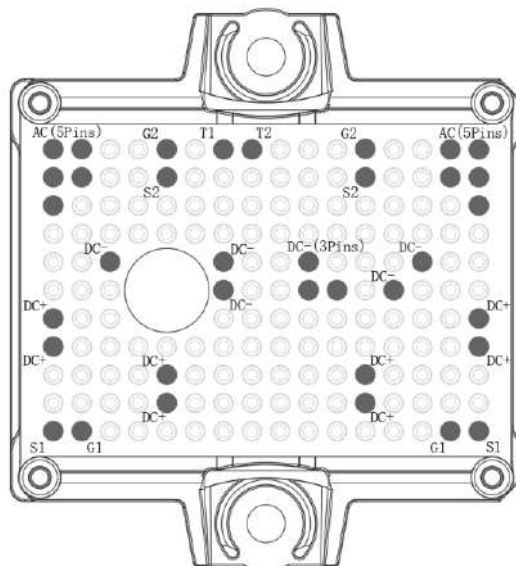


Figure 2. Pin configuration

PIN No.	Symbol	Description
1-5(5pins)	AC	Output terminal of half bridge
6	S2	Low side source signal terminal
7	G2	Low side gate signal terminal
8	T 1	Thermistor connection 1
9	T2	Thermistor connection 2
10	S2	Low side source signal terminal
11	G2	Low side gate signal terminal
12-16(5pins)	AC	Output terminal of half bridge
17-24(8pins)	DC -	DC – Bus connection
25-32(8pins)	DC +	DC + Bus connection
33	S1	High sidesource signal terminal
34	G 1	High side gate signal terminal
35	G1	High side gate signal terminal
36	S1	High sidesource signal terminal

Module

Parameter	Conditions	Value	Unit
Isolation voltage	RMS, f = 50Hz, t =1min	3.4	kV
Clearance	Terminal to Terminal	5	mm
	Terminal to Heatsink	10	mm
Creepage distance	Terminal to Terminal	6.3	mm
	Terminal to Heatsink	12.7	mm
Comparative Tracking Index	—	400	—

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Maximum Ratings ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	DrainSource Voltage	G-S Short	1200	V
V_{GS}	G-S Voltage	D-S Short, Note1	-10 to 20	V
I_{DS}	DC Continuous Drain Current	$T_f=90^{\circ}\text{C}$	200	A
I_{SD}	Source (Body diode) Current	$T_f=90^{\circ}\text{C}$ with ON signal	200	A
I_{DP}	Drain Pulse Current, Peak	Less than 1ms, Note 2	400	A
T_j	junction temperature	-	-40 to 175	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	-40 to 125	$^{\circ}\text{C}$

Note1: Recommended Operating Value, -5V/+15V.

Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R_{25}	Resistance	$T_C=25^{\circ}\text{C}$	-	5	-	kΩ
R/R	Deviation of R100	$T_C=100^{\circ}\text{C}$, $R_{100}=493\Omega$	5	-	5	%
P_{25}	Power dissipation	$T_C=25^{\circ}\text{C}$	-	-	20	mW
$B_{25/50}$	B-value	$R_{25}=R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	-	3375	-	K
$B_{25/80}$	B-value	$R_{25}=R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	-	3411	-	K
$B_{25/100}$	B-value	$R_{25}=R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	-	3433	-	K

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MOSFET Electrical characteristics ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =300uA		1200	—	—	V
I _{DSS}	Zero gate voltage drain Current	V _{DS} =1200V, V _{GS} =0V		—	3	—	μA
V _{GS(th)}	Gate-source threshold Voltage	I _D =105mA, V _{DS} =V _{GS} , T _j =25° C		1.8	2.7	—	V
		I _D =105mA, V _{DS} =V _{GS} , T=175° C		—	2.05	—	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V, V _{DS} =0V, T _j =25° C		—	300	—	nA
R _{DS(on)} (Chip)	Static drain-source On-state resistance	I _D =200A	T _j =25° C	—	6.5	9	m Ω
		V _{GS} =15V	T _j =175° C	—	9.6	—	m Ω
V _{DS(on)} (Chip)	Static drain source On-state Voltage	I _D =200A	T _j =25° C	—	1.30	1.8	V
		V _{GS} =15V	T _j =175° C	—	1.92	—	V
C _{iss}	Input Capacitance	V _D =800V, V _{GS} =0V f=1M Hz, V _{AC} =25mV		—	17.4	—	nF
C _{oss}	OutputCapacitance			—	0.528	—	nF
C _{rss}	Reverse transfer Capacitance			—	0.042	—	nF
Q _G	Total gate charge	V _{DD} =800V, I _D =180A, V _{GS} =-5/+15V		—	540	—	nC
R _{Gint}	Internal Gate Resistance	f =1Mhz, V _{AC} =25m V		—	0.43	—	Ω
t _{d(on)}	Turn-on delay time	V _{DD} =600V I _D =200A V _{GS} =-5/+ 15V R _G =3.3 Ω Inductive load switching operation	T _j =25° C	—	31	—	ns
			T _j =150° C	—	28	—	
t _r	Rise time		T _j =25° C	—	18	—	ns
			T _j =150° C	—	18	—	
t _{d(off)}	Turn-offdelay time		T _j =25° C	—	101	—	ns
			T _j =150° C	—	119	—	
t _f	Fall time		T _j =25° C	—	38	—	ns
			T _j =150° C	—	42	—	
E _{on}	Turn-on power dissipation		T _j =25° C	—	4.45	—	mJ
			T _j =150° C	—	4.82	—	
E _{off}	Turn-offpower dissipation		T _j =25° C	—	2.01	—	mJ
			T _j =150° C	—	2.22	—	
R _{th(j)}	FET Thermal Resistance	Junction to Case/MOSFET		—	0.1	—	K/W
R _{th(cf)}	Contact thermal resistance	With thermal conductivegrease /MOSFET		—	0.12	—	K/W

Assumes Thermal Conductivity of grease is 2.8 W/mK and thickness is 50μm.

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Body Diode Electrical characteristics $T_j=25^{\circ}\text{C}$ unless otherwise specified, chip:Target)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{SD}	Body Diode Forward Voltage	V _{GS} =-5V I _{SD} =200A	T _j =25° C	—	5.4	—	V
			T _j =175° C	—	5.0	—	
T _{rr}	Reverse recovery time	V _{DD} =600V I _D =200A	T _j =25° C	—	56	—	ns
			T _j =150° C	—	48	—	
Q _{rr}	Reverse recovery charge	V _{GS} =-5/+15V R _G =3.3 Ω	T _j =25° C	—	3.03	—	μC
			T _j =150° C	—	6.21	—	
E _{rr}	Diode switching powe dissipation	Inductive load switching operation	T _j =25° C	—	0.92	—	mJ
			T _j =150° C	—	1.86	—	

Test Conditions

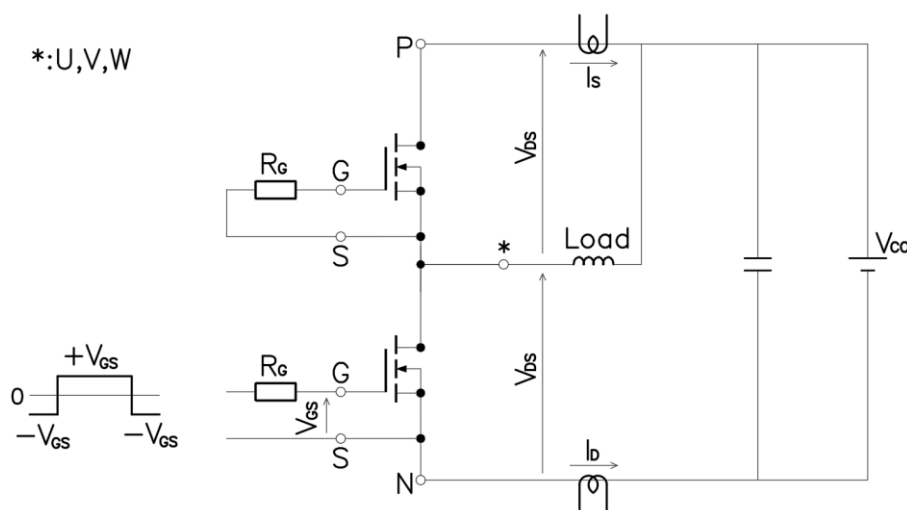


Figure 3. Switching time measure circuit

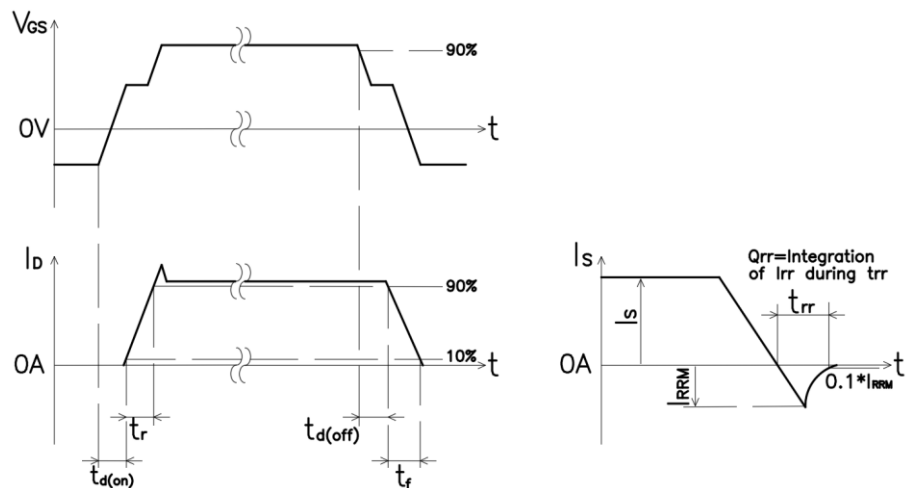


Figure 4. Switching time definition

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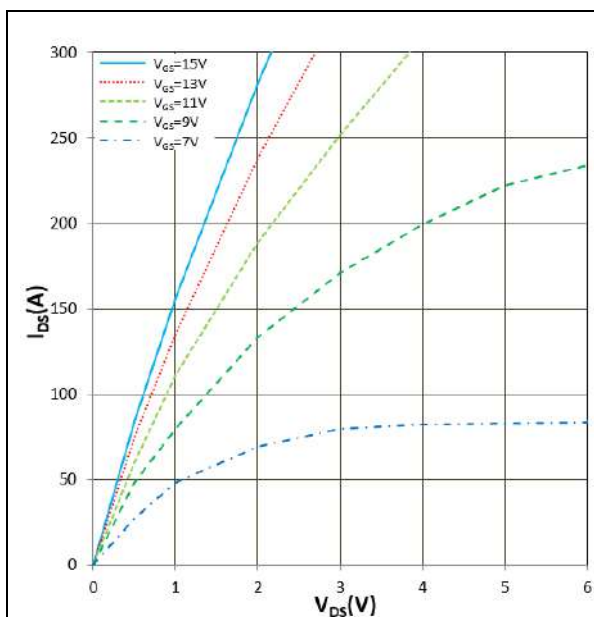


Figure 5. I_{DS} vs V_{DS}
 $T_j = 25^\circ\text{C}$ ζV_{GS} parameter

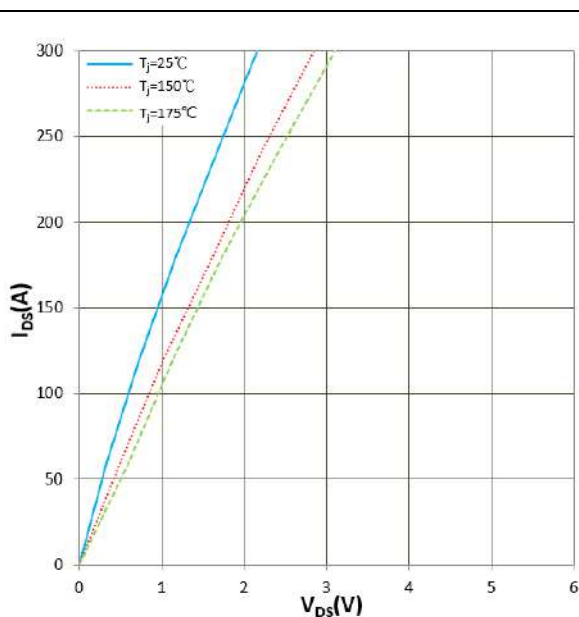


Figure 6. I_{DS} vs V_{DS}
 $V_{GS} = +15\text{V}$

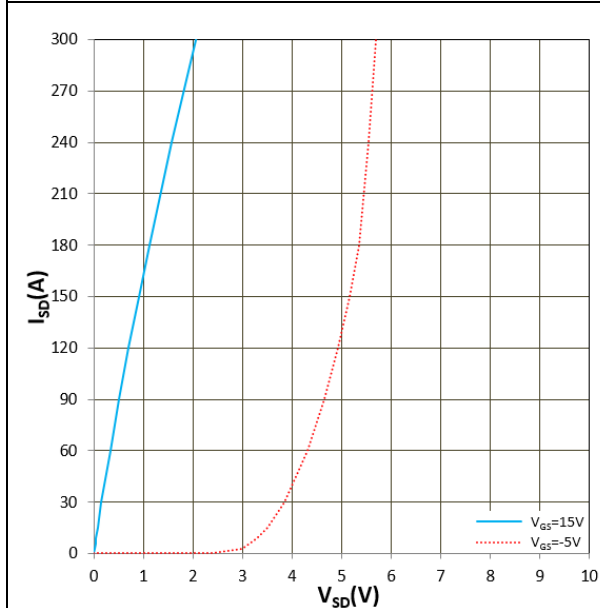


Figure 7. S_D vs V_{SD} (V_F)
 $T_j = 25^\circ\text{C}$ ζV_{GS} parameter

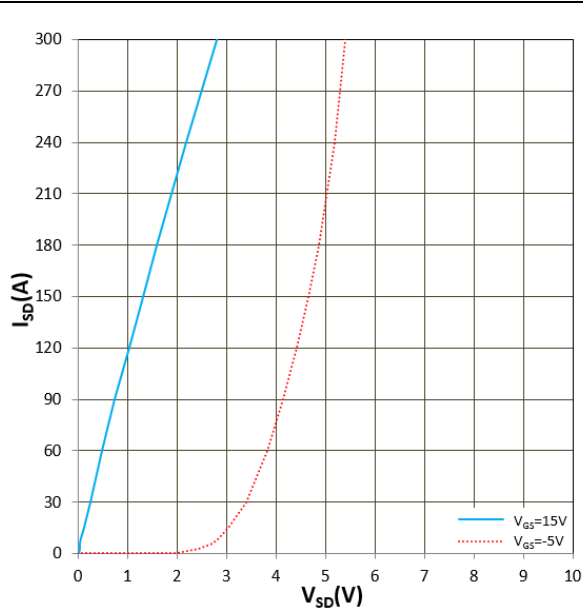


Figure 8. S_D vs V_{SD} (V_F)
 $T_j = 175^\circ\text{C}$ ζV_{GS} parameter

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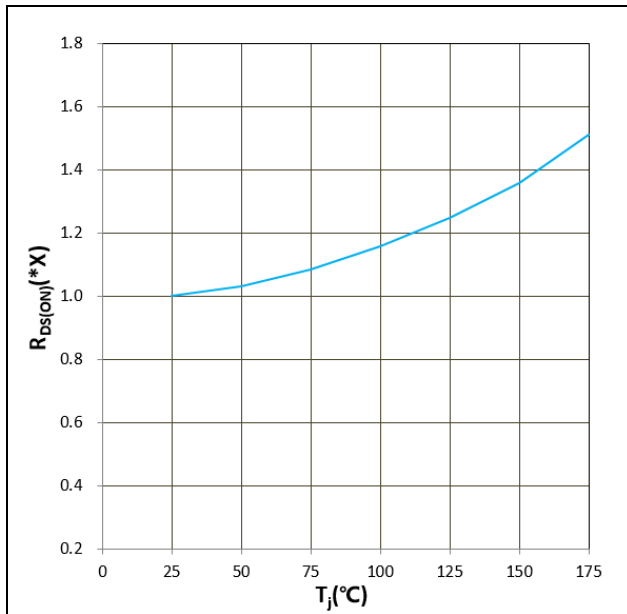


Figure9. $R_{DS(on)}$ vs T_j
 $V_{GS} = +15V$, $I_D = 200A$, $1.0X \ 6.5m\Omega$

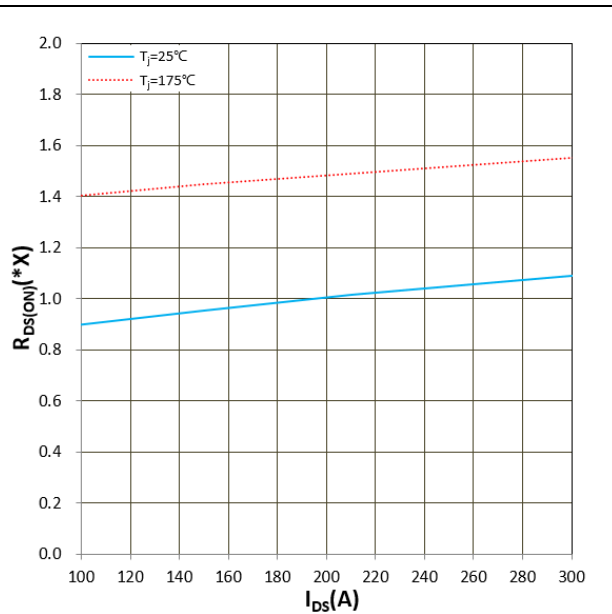


Figure10. $R_{DS(on)}$ vs I_{DS}
 $V_{GS} = +15V$, $1.0X \ 6.5m\Omega$

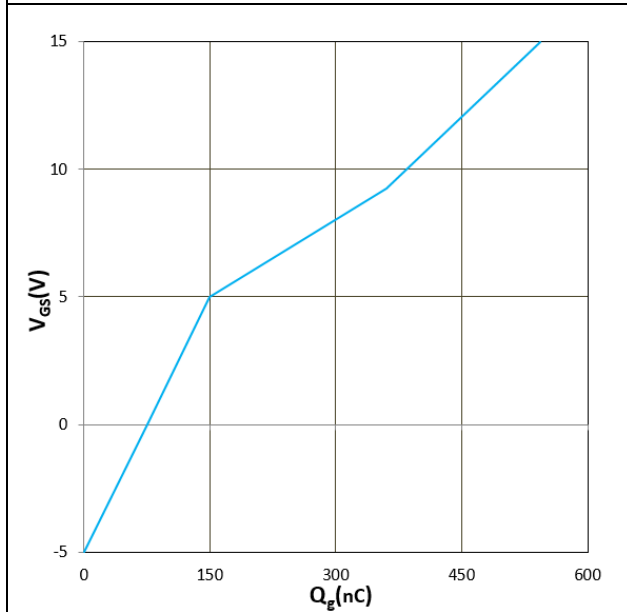


Figure11. V_{GS} vs Q_g
 $V_{DS} = 800V$, $I_D = 180A$, $T_j = 25^\circ C$

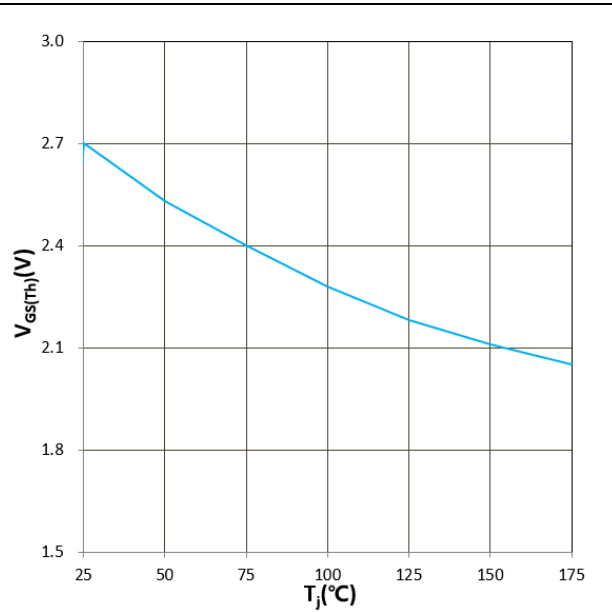


Figure12. $V_{GS(th)}$ vs T_j
 $V_{GS} = V_{DS}$, $I_D = 105mA$

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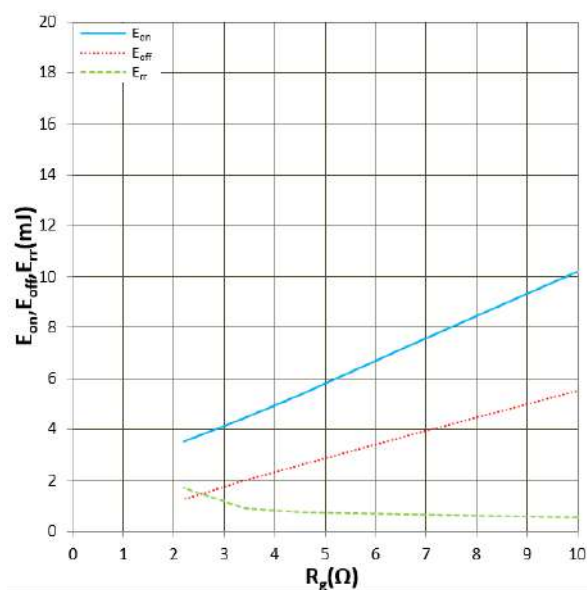


Figure13. E_{on} , E_{off} , E_r vs R_g

$T_j=25^{\circ}\text{C}$, $V_{CC}=600\text{V}$, $I_D=200\text{A}$, $V_{GS}=-5\text{V}/+15\text{V}$
Inductive Load

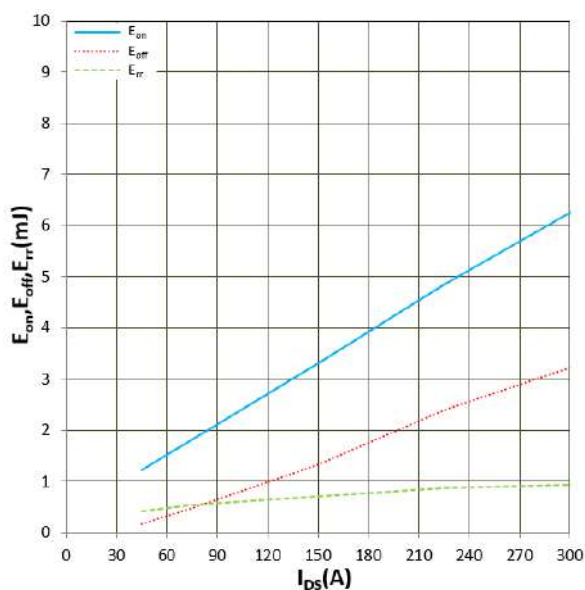


Figure14. E_{on} , E_{off} , E_r vs I_{DS}

$T_j=25^{\circ}\text{C}$, $V_{CC}=600\text{V}$, $R_g=3.3\Omega$, $V_{GS}=-5\text{V}/+15\text{V}$
Inductive Load

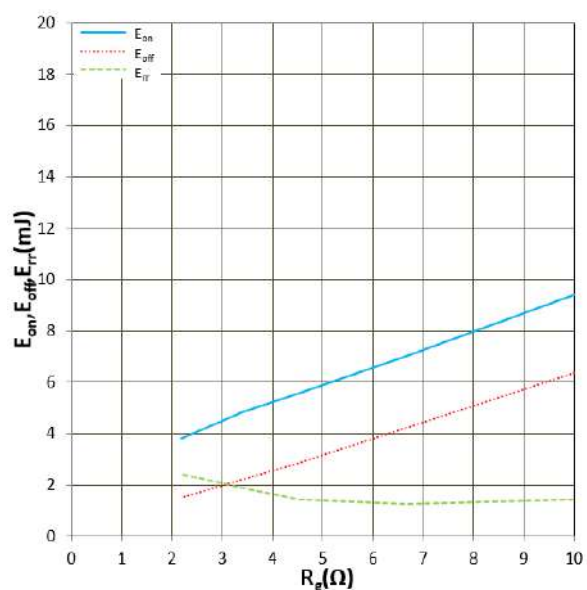


Figure15. E_{on} , E_{off} , E_r vs R_g

$T_j=150^{\circ}\text{C}$, $V_{CC}=600\text{V}$, $I_D=200\text{A}$, $V_{GS}=-5\text{V}/+15\text{V}$
Inductive Load

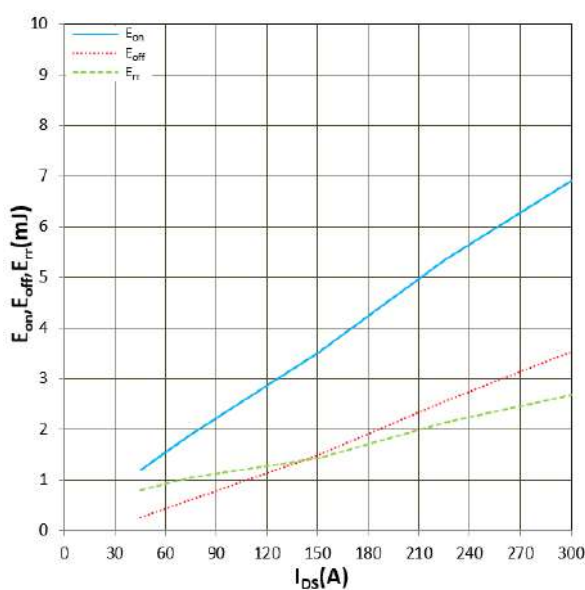


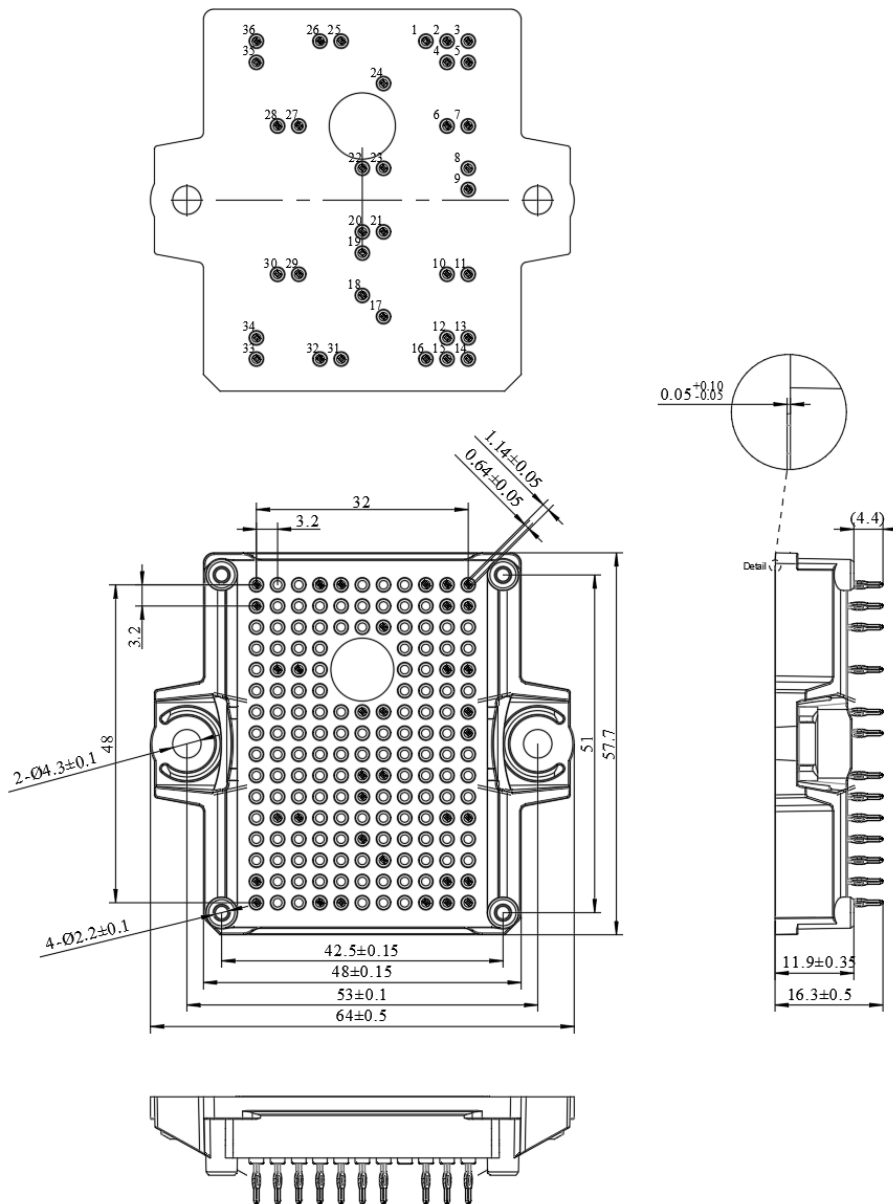
Figure16. E_{on} , E_{off} , E_r vs I_{DS}

$T_j=150^{\circ}\text{C}$, $V_{CC}=600\text{V}$, $R_g=3.3\Omega$, $V_{GS}=-5\text{V}/+15\text{V}$
Inductive Load

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Package dimensions



Pin	X	Y
1	25,6	48
2	28,8	48
3	32	48
4	28,8	44,8
5	32	44,8
6	28,8	35,2
7	32	35,2
8	32	28,8
9	32	25,6
10	28,8	12,8
11	32	12,8
12	28,8	3,2
13	32	3,2
14	32	0
15	28,8	0
16	25,6	0
17	19,2	6,4
18	16	9,6
19	16	16
20	16	19,2
21	19,2	19,2
22	16	28,8
23	19,2	28,8
24	19,2	41,6
25	12,8	48
26	9,6	48
27	6,4	35,2
28	3,2	35,2
29	6,4	12,8
30	3,2	12,8
31	12,8	0
32	9,6	0
33	0	0
34	0	3,2
35	0	44,8
36	0	48

Unit: mm

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IMPORTANT NOTICE:

This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

The data contained in this document is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the product's suitability for the intended application and the completeness of the product data concerning such application.

Due to technical requirements, our product may contain dangerous substances. For information on the types in question, please contact the sales staff responsible for you.

Changes to this product data sheet are reserved.

Please contact the sales staff (sales@hiitio.com) for further information on the product, technology, delivery terms, conditions and prices. □

Revision History

Document Version	Description of Changes
RevX.0.1	Released

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